

MANUFACTURE OF SEMICONDUCTOR LIGHT-EMITTING ELEMENT

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Abstract

PROBLEM TO BE SOLVED: To provide the manufacture of a semiconductor light-emitting element which is capable of manufacturing a flat panel display enabling light emission in multiple colors and having high luminance and high level of fineness.

SOLUTION: A semiconductor layer, consisting of an InGaN material is laminated on a substrate in the manufacture of the semiconductor light-emitting element, a second semiconductor layer 4 composed of AlN or In_y Ga_{1-y} N (0<=y<=1) grown at a temperature lower than a first semiconductor layer, is formed onto a first semiconductor layer 3 consisting on In_x Ga_{1-x} N (0<=x<=1), and a third semiconductor layer 5, consisting of In_z Ga_{1-z} N (0<=z<=1) grown at a temperature higher than that of the second semiconductor layer is formed on the second semiconductor layer.

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